



Product Overview

NTMFS4C09N: Power MOSFET 30V 52A 5.8 mOhm Single N-Channel S0-8FL

For complete documentation, see the data sheet

Product Description

NTMFS4C09N

Features

- Low RDS(on) to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are PbFree and are RoHS Compliant

Applications

- CPU Power Delivery
- DCDC Converters

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	V _{DS} (BR) Min (V)	V _{GS} Max (V)	V _{GS} (th) Max (V)	I _D Max (A)	P _D Max (W)	r _{DS(on)} Max @ V _{GS} = 2.5 V (m)	r _{DS(on)} Max @ V _{GS} = 4.5 V (m)	r _{DS(on)} Max @ V _{GS} = 10 V (m)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	Q _{gd} Typ @ V _{GS} = 4.5 V (nC)	Q _{rr} Typ (nC)	C _{iss} Typ (pF)	C _{oss} Typ (pF)	C _{rss} Typ (pF)	Packaging Type
NTMFS4C09NT1G	Pb-free Halide free	Active	N-Channel	Single	30	20	2.1	52	25.5		8.5	5.8		22.2	5.4	15	1252	610	126	SO-8FL / DF N-5
NTMFS4C09NT3G	Pb-free Halide free	Active	N-Channel	Single	30	20	2.1	52	25.5		8.5	5.8		22.2	5.4	15	1252	610	126	SO-8FL / DF N-5

For more information please contact your local sales support at www.onsemi.com

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